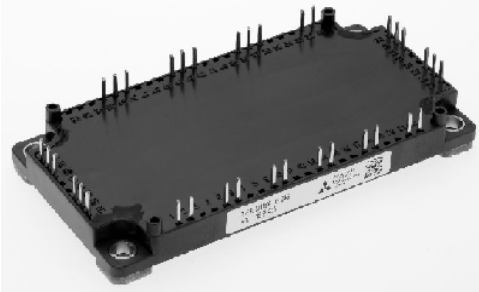


<IGBT Modules>

CM150TX-24S

**HIGH POWER SWITCHING USE
INSULATED TYPE**



sixpack (3φ Inverter)

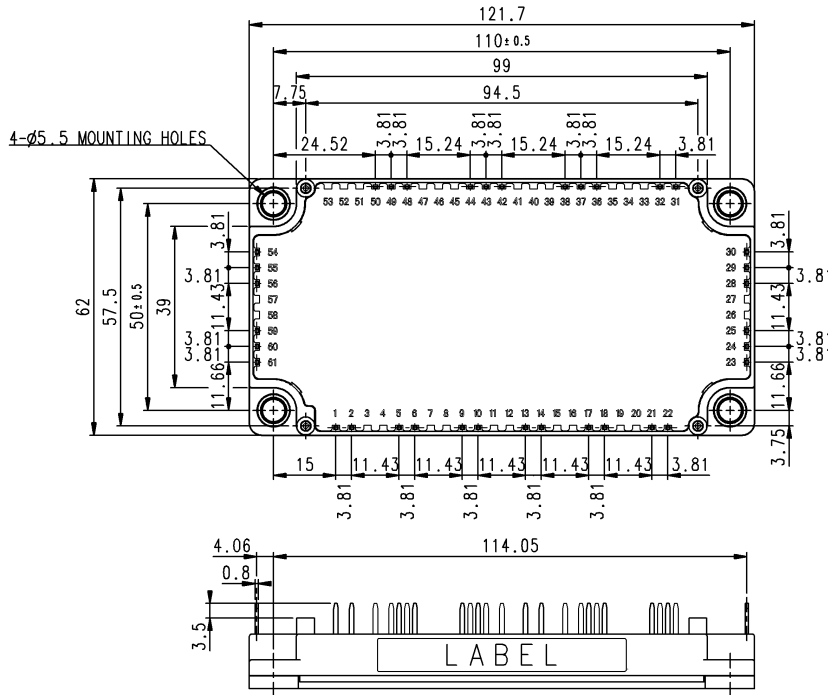
Collector current I_C **1 5 0 A**
 Collector-emitter voltage V_{CES} **1 2 0 0 V**
 Maximum junction temperature T_{jmax} **1 7 5 °C**

- Flat base Type
- Copper base plate (non-plating)
- Tin plating pin terminals
- RoHS Directive compliant
- Recognized under UL1557, File E323585

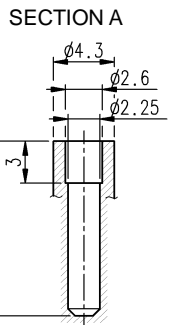
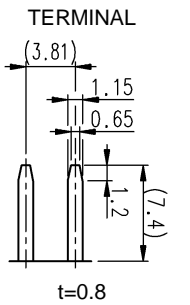
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

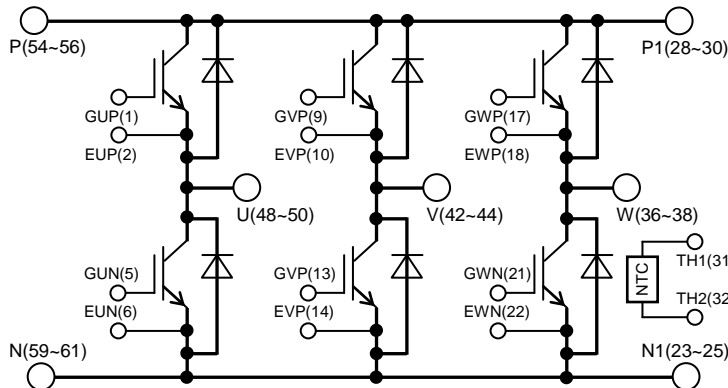
OUTLINE DRAWING & INTERNAL CONNECTION



Dimension in mm



INTERNAL CONNECTION



Caution: Each (three) pin terminal of P/N/P1/N1/U/V/W is connected in the module, but should use all each three pins for the external wiring.

Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

The tolerance of size between terminals is assumed to be ±0.4.

CM150TX-24S

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=120\text{ }^\circ\text{C}$ (Note2, 4)	150	A
I_{CRM}		Pulse, Repetitive (Note3)	300	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note2, 4)	1150	W
I_E (Note1)	Emitter current	DC (Note2)	150	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	300	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	2500	V
T_{jmax}	Maximum junction temperature	Instantaneous event (overload)	175	$^\circ\text{C}$
T_{Cmax}	Maximum case temperature	(Note4)	125	$^\circ\text{C}$
T_{jop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1.0	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=15\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
V_{CESat} (Terminal)	Collector-emitter saturation voltage	$I_C=150\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit. (Note6)	$T_j=25\text{ }^\circ\text{C}$	-	1.80	2.25	V
V_{CESat} (Chip)			$T_j=125\text{ }^\circ\text{C}$	-	2.00	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.05	-	
		V_{CESat} (Chip)	$I_C=150\text{ A}$, $V_{GE}=15\text{ V}$, (Note6)	$T_j=25\text{ }^\circ\text{C}$	-	1.70	2.15
$T_j=125\text{ }^\circ\text{C}$				-	1.90	-	
$T_j=150\text{ }^\circ\text{C}$				-	1.95	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	15	nF	
C_{oes}	Output capacitance		-	-	3.0		
C_{res}	Reverse transfer capacitance		-	-	0.25		
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $V_{GE}=15\text{ V}$	-	350	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load	-	-	800	ns	
t_r	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	600		
t_f	Fall time		-	-	300		
V_{EC} (Note1) (Terminal)	Emitter-collector voltage	$I_E=150\text{ A}$, G-E short-circuited, Refer to the figure of test circuit. (Note6)	$T_j=25\text{ }^\circ\text{C}$	-	1.80	2.25	V
V_{EC} (Note1) (Chip)			$T_j=125\text{ }^\circ\text{C}$	-	1.80	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.80	-	
		V_{EC} (Note1) (Chip)	$I_E=150\text{ A}$, G-E short-circuited, (Note6)	$T_j=25\text{ }^\circ\text{C}$	-	1.70	2.15
$T_j=125\text{ }^\circ\text{C}$				-	1.70	-	
$T_j=150\text{ }^\circ\text{C}$				-	1.70	-	
t_{rr} (Note1)	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_E=150\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load	-	-	300	ns	
Q_{rr} (Note1)	Reverse recovery charge	$R_G=0\text{ }\Omega$, Inductive load	-	8.0	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C=I_E=150\text{ A}$,	-	24.2	-	mJ	
E_{off}	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$,	-	16	-		
E_{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	12.2	-	mJ	
$R_{CC+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4)	-	-	1.8	m Ω	
r_g	Internal gate resistance	Per switch	-	13	-	Ω	

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HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified) NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R ₂₅	Zero-power resistance	T _C =25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R ₁₀₀ =493 Ω, T _C =100 °C (Note4)	-7.3	-	+7.8	%
B _(25/50)	B-constant	Approximate by equation (Note6)	-	3375	-	K
P ₂₅	Power dissipation	T _C =25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	0.13	K/W
R _{th(j-c)D}		Junction to case, per Inverter DIODE (Note4)	-	-	0.23	
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, per 1 module, Thermal grease applied (Note4, 7)	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d _s	Creepage distance	Terminal to terminal	10.28	-	-	mm
		Terminal to base plate	12.41	-	-	
d _a	Clearance	Terminal to terminal	9.88	-	-	mm
		Terminal to base plate	12.41	-	-	
m	mass	-	-	300	-	g
e _c	Flatness of base plate	On the centerline X, Y (Note8)	±0	-	+100	μm

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (DIODE).

2. Junction temperature (T_j) should not increase beyond T_{jmax} rating.

3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.

4. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.

5. Pulse width and repetition rate should be such as to cause negligible temperature rise.

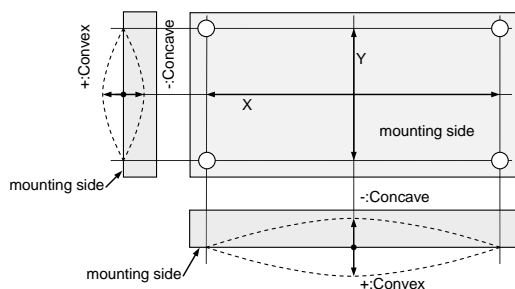
$$6. B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right),$$

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).

8. The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



9. Use the following screws when mounting the printed circuit board (PCB) on the stand offs.

"φ2.6×10 or φ2.6×12 self tapping screw"

The length of the screw depends on the thickness (t1.6~t2.0) of the PCB.

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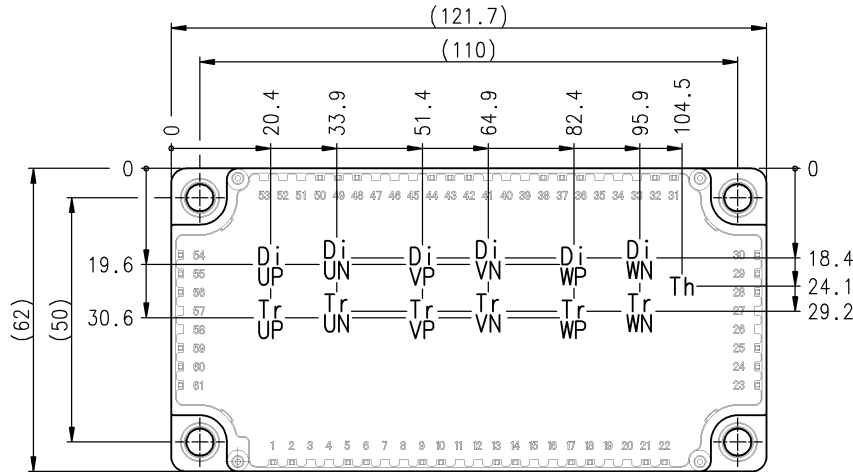
HIGH POWER SWITCHING USE
INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across P-N/P1-N1 terminals	-	600	850	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G*P-E*P/G*N-E*N (*=U, V, W) terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0	-	30	Ω

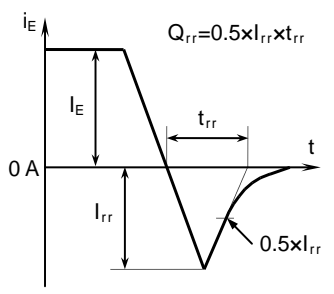
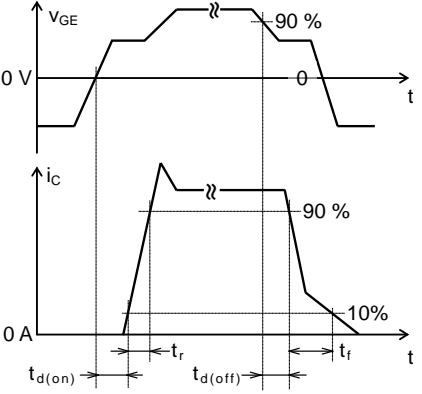
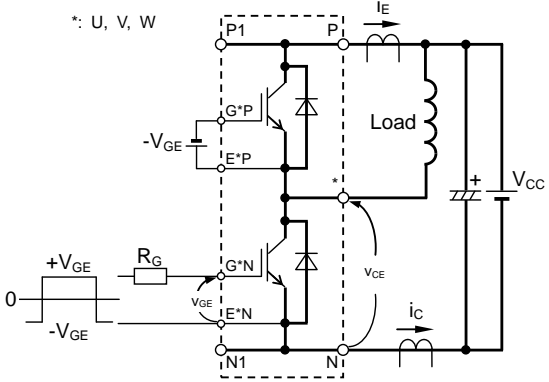
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm



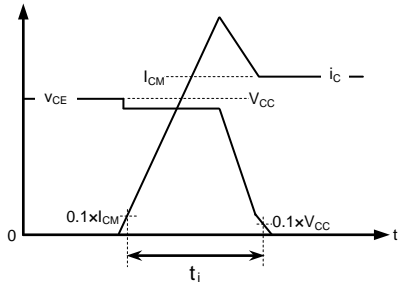
Tr*P/Tr*N: IGBT, Di*P/Di*N: DIODE (*=U/V/W), Th: NTC thermistor

TEST CIRCUIT AND WAVEFORMS

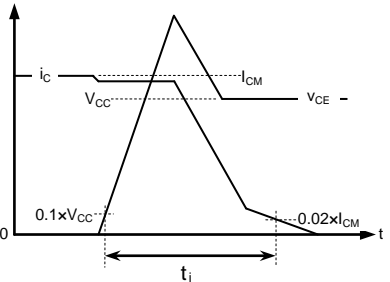


Switching characteristics test circuit and waveforms

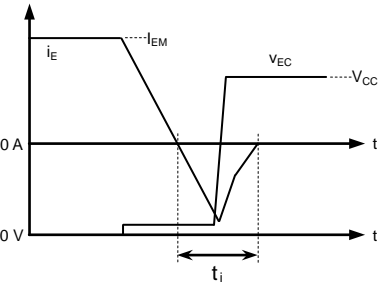
t_{rr} , Q_{rr} test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



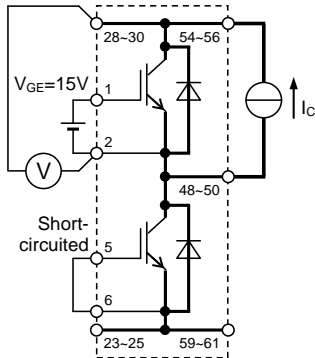
DIODE Reverse recovery energy

Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

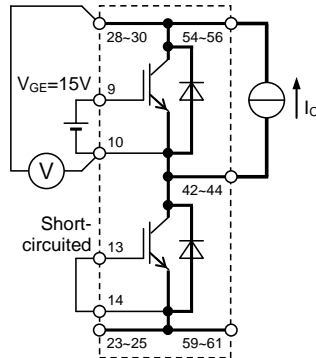
CM150TX-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

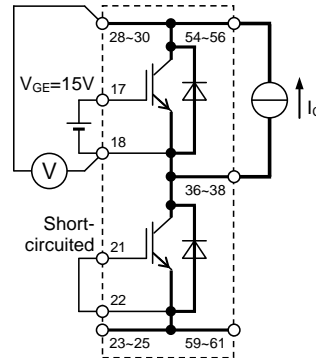
TEST CIRCUIT



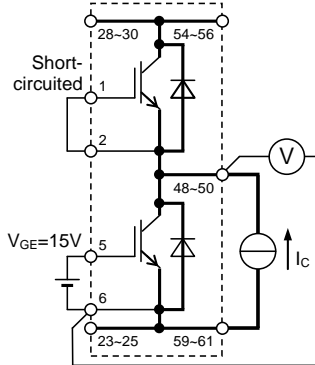
Gate-emitter GVP-EVP, GVN-EVP,
short-circuited GWP-EWN, GWN-EWN
UP / UN IGBT



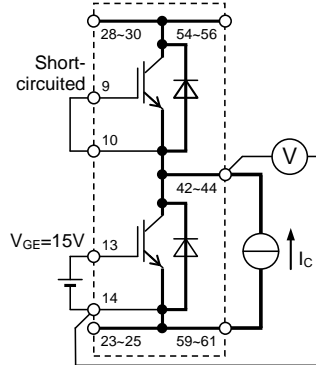
Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN
VP / VN IGBT



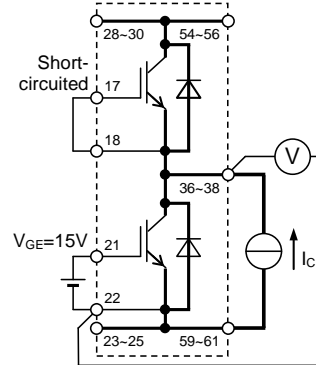
Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN
WP / WN IGBT



Gate-emitter GVP-EVP, GVN-EVP,
short-circuited GWP-EWN, GWN-EWN
UP / UN DIODE

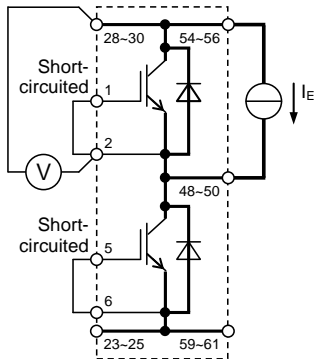


Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN
VP / VN DIODE

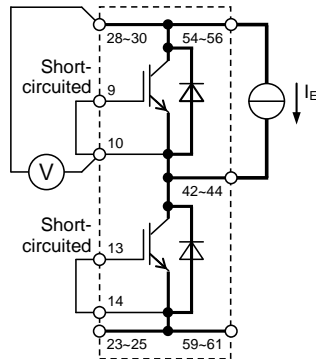


Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN
WP / WN DIODE

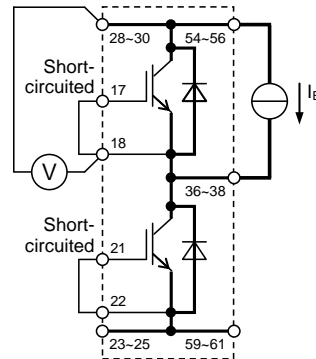
V_{CEsat} test circuit



Gate-emitter GVP-EVP, GVN-EVP,
short-circuited GWP-EWN, GWN-EWN
UP / UN DIODE



Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN
VP / VN DIODE



Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN
WP / WN DIODE

V_{EC} test circuit

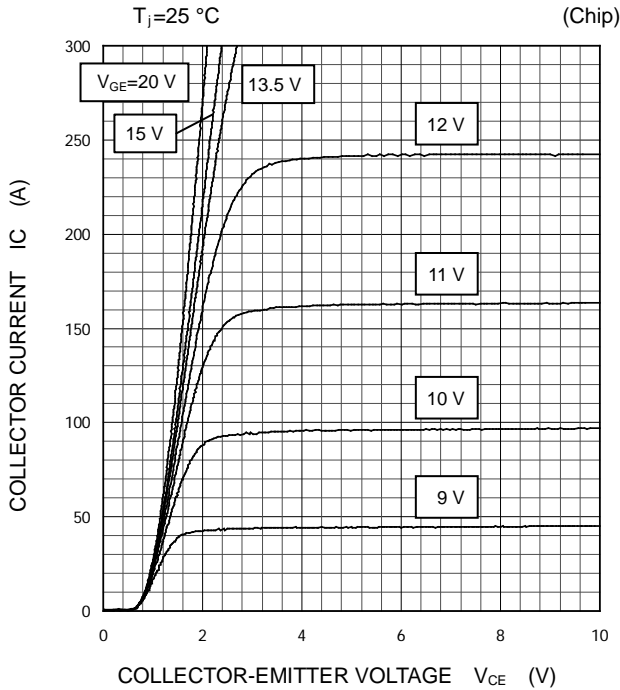
CM150TX-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

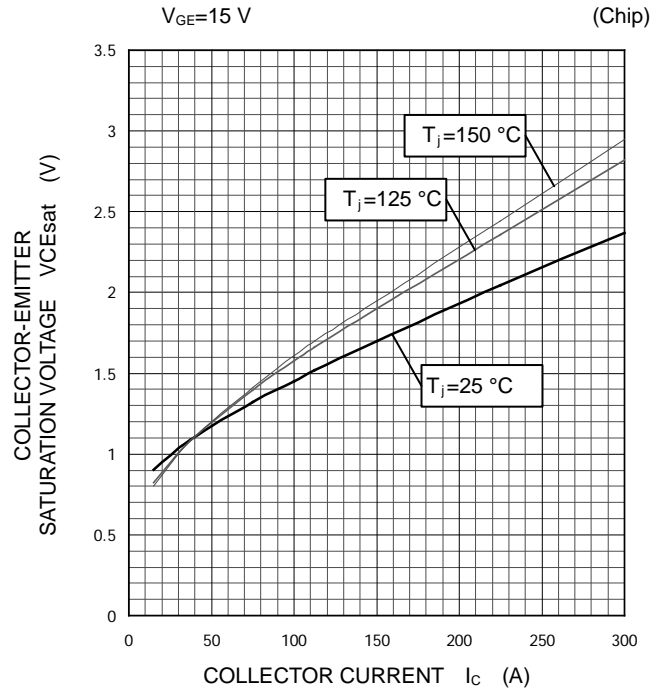
PERFORMANCE CURVES

INVERTER PART

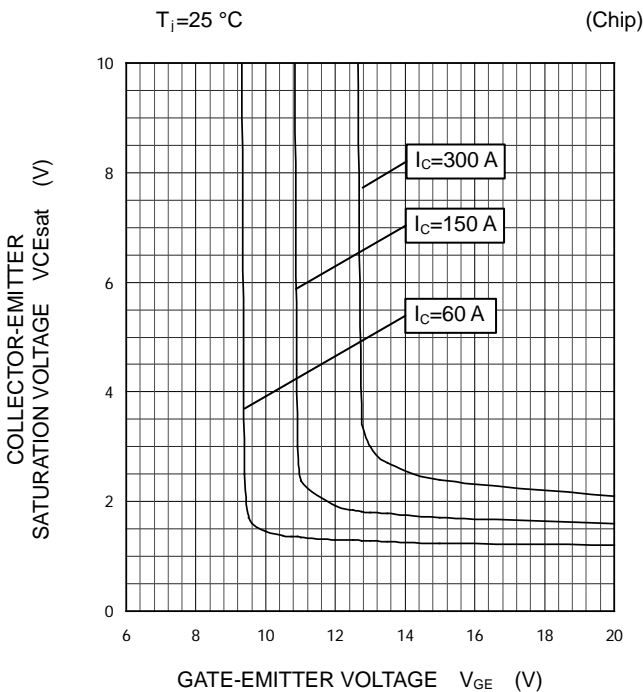
OUTPUT CHARACTERISTICS
(TYPICAL)



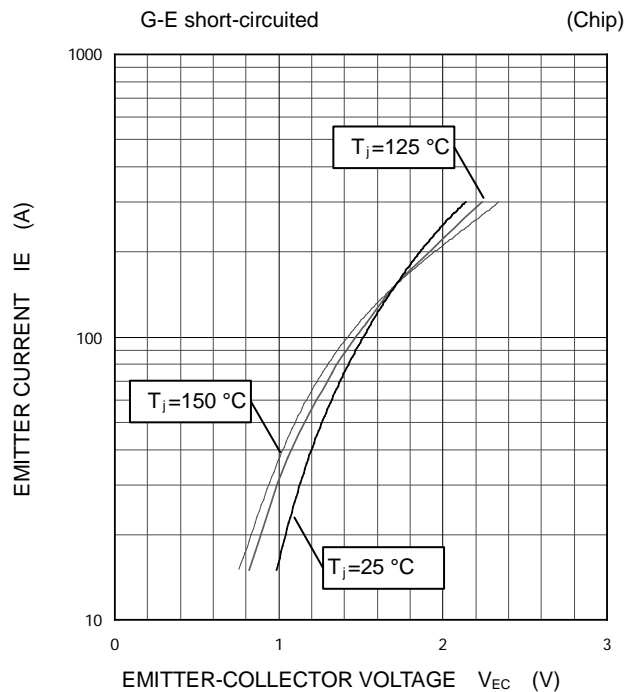
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS
(TYPICAL)



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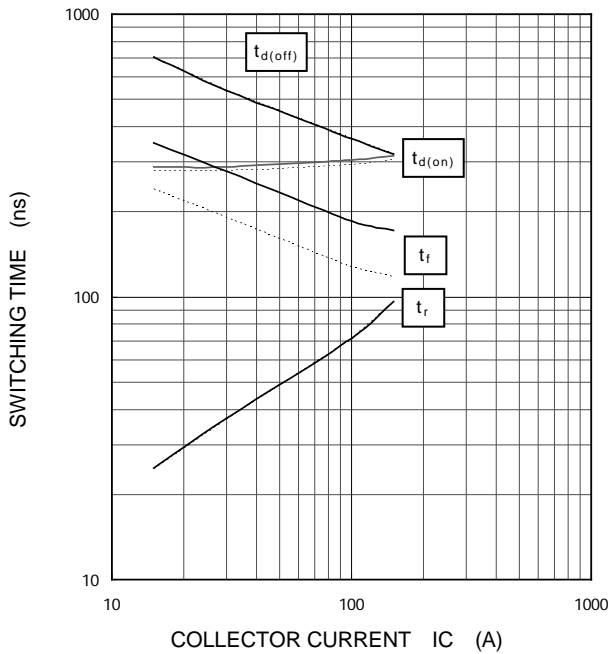
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

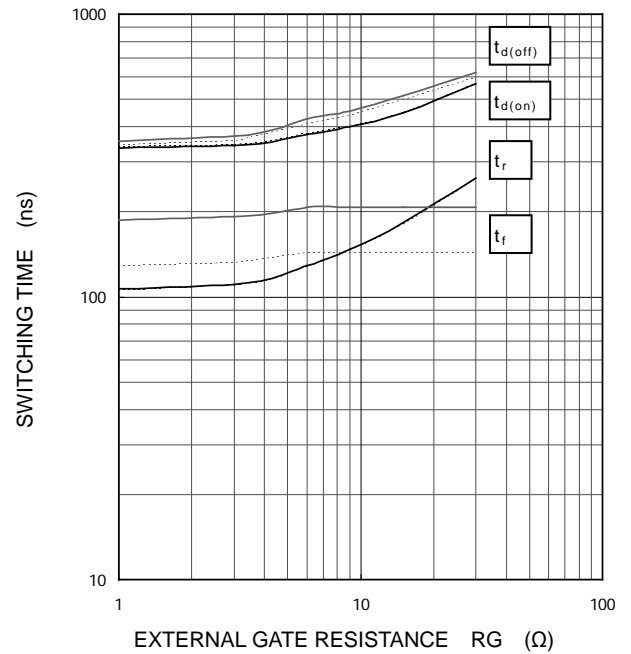
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



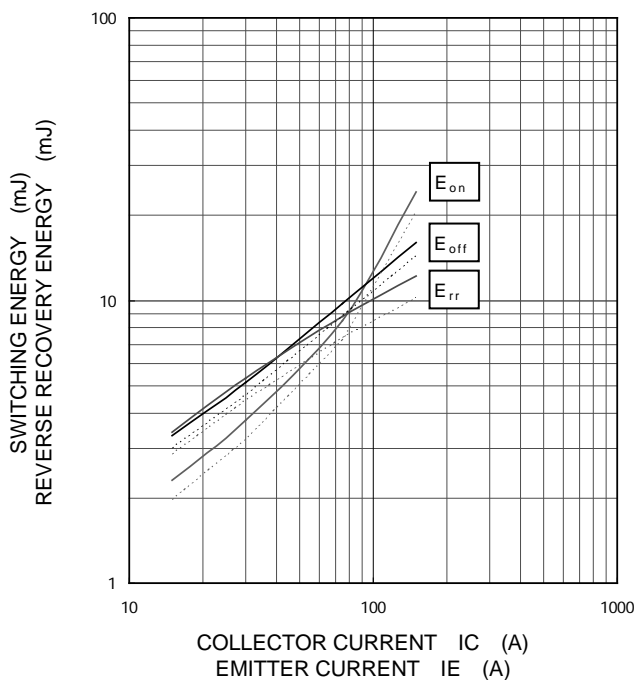
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=150\text{ A}$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



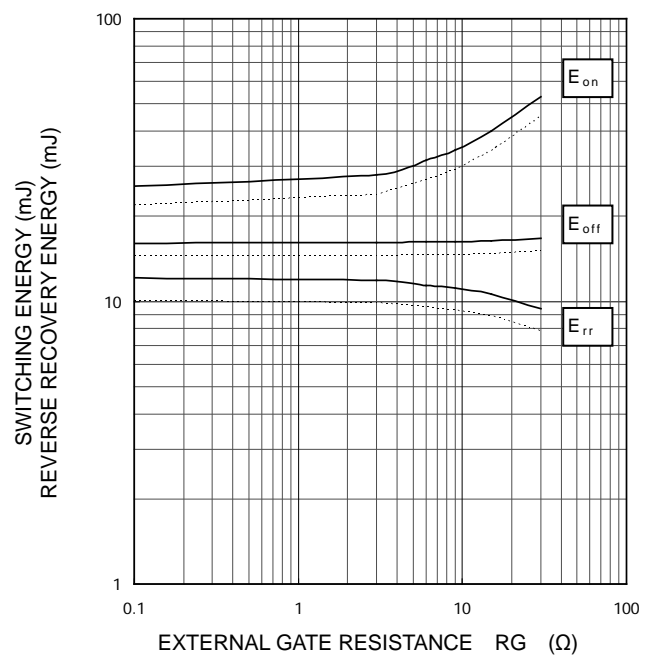
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
INDUCTIVE LOAD, PER PULSE
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C/I_E=150\text{ A}$,
INDUCTIVE LOAD, PER PULSE
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



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HIGH POWER SWITCHING USE
INSULATED TYPE

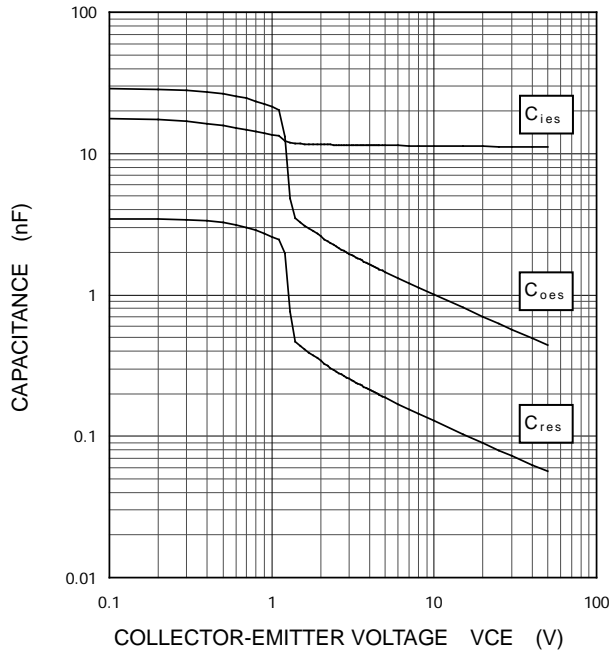
PERFORMANCE CURVES

INVERTER PART

CAPACITANCE CHARACTERISTICS

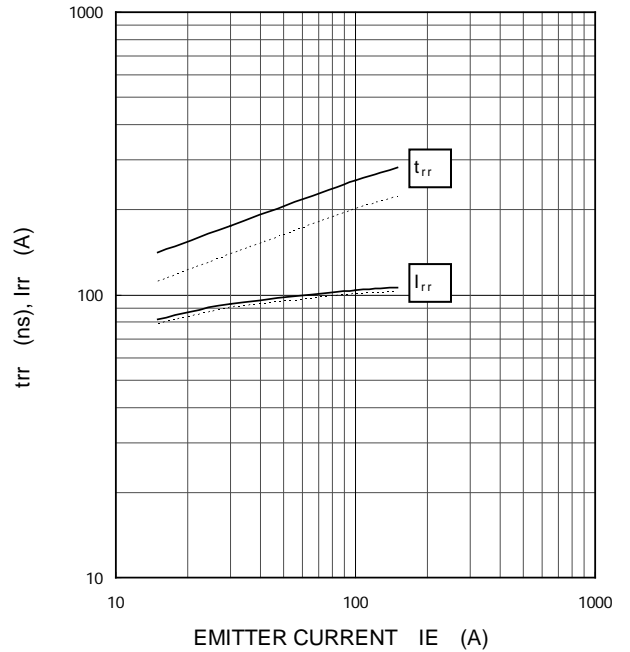
(TYPICAL)

G-E short-circuited, $T_j=25\text{ }^\circ\text{C}$



FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

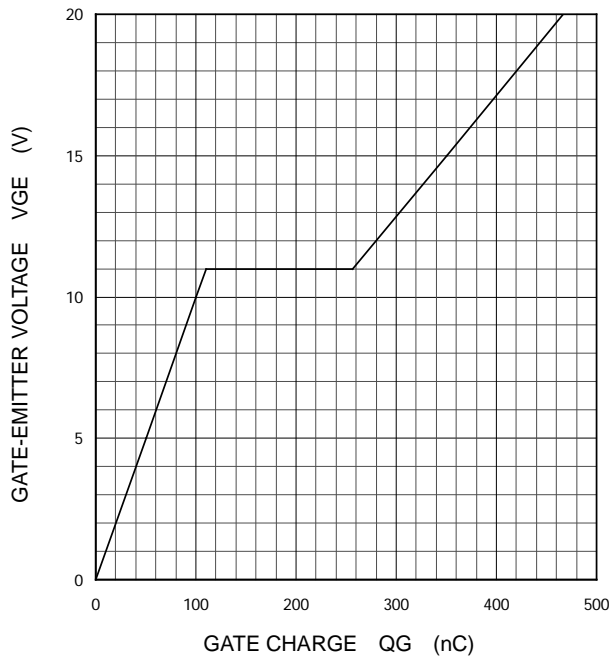
$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
—: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



GATE CHARGE CHARACTERISTICS

(TYPICAL)

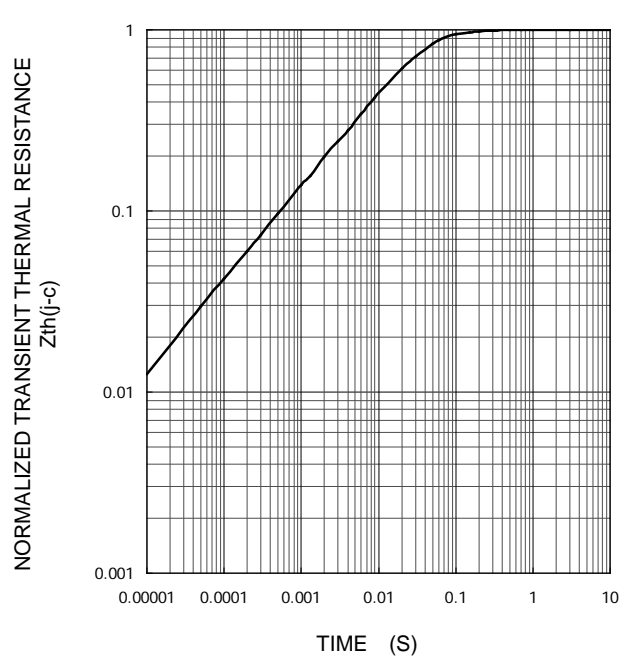
$V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $T_j=25\text{ }^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

(MAXIMUM)

Single pulse, $T_c=25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q}=0.13\text{ K/W}$, $R_{th(j-c)D}=0.23\text{ K/W}$



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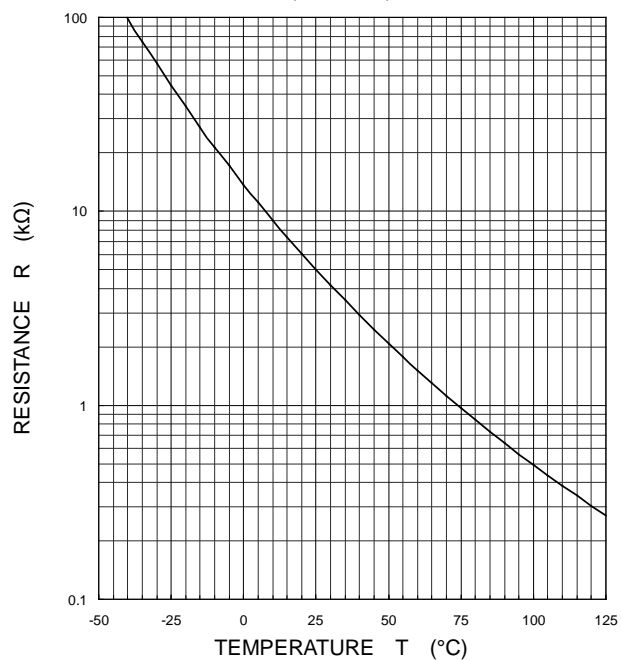
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part

TEMPERATURE CHARACTERISTICS

(TYPICAL)



Important Notice

The information contained in this datasheet shall in no event be regarded as a guarantee of conditions or characteristics. This product has to be used within its specified maximum ratings, and is subject to customer's compliance with any applicable legal requirement, norms and standards.

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